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About bond model of S-type negative differential resistance in GaP LEDs

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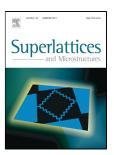
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ACCEPTED MANUSCRIPT Highlights

- There are two negative differential resistance regions in CVC of GaP LEDs
- The NDR lower part might be due to internally electron transfer E_1^C to E_3^C
- The development of the NDR ($T \le 120K$) is provided by the positive internal bond

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